

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

2SC2412R-MS

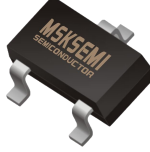

Product specification

TRANSISTOR (NPN)

FEATURE

- Low Cob ,Cob = 2.0 pF (Typ).

Reference News

SOT-23	MARKING
 <ol style="list-style-type: none"> 1. BASE 2. EMITTER 3. COLLECT 	

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current -Continuous	150	mA
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =1mA	180		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.4	V
Transition frequency	f _T	V _{CE} =12V, I _C =-2mA, f=100MHz		160		MHz
Collector output capacitance	C _{ob}	V _{CB} =12V, I _E =0, f=1MHz		2.0	3.5	pF

Typical Characteristics

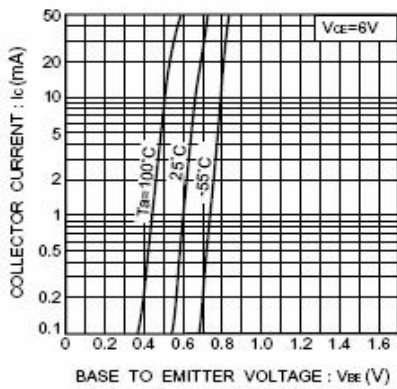


Fig.1 Grounded emitter propagation characteristics

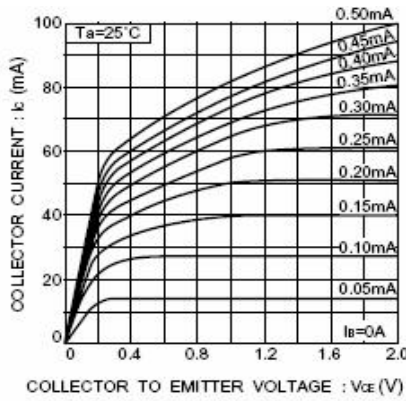


Fig.2 Grounded emitter output characteristics (I)

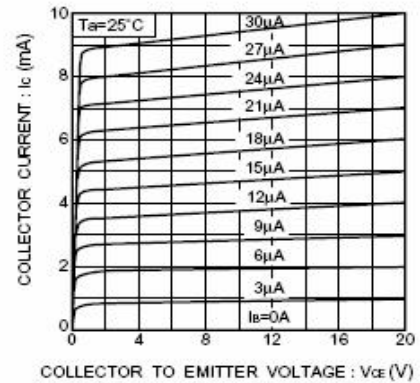


Fig.3 Grounded emitter output characteristics (II)

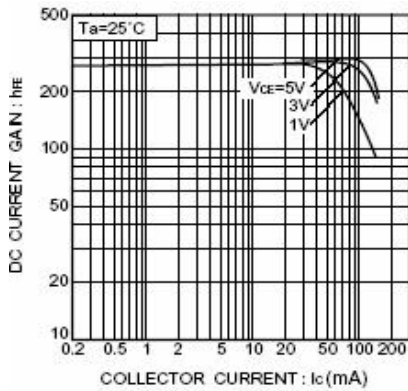


Fig.4 DC current gain vs. collector current (I)

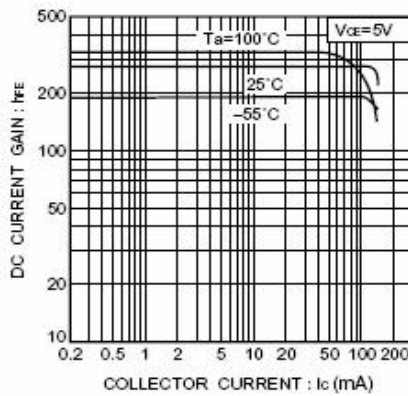


Fig.5 DC current gain vs. collector current (II)

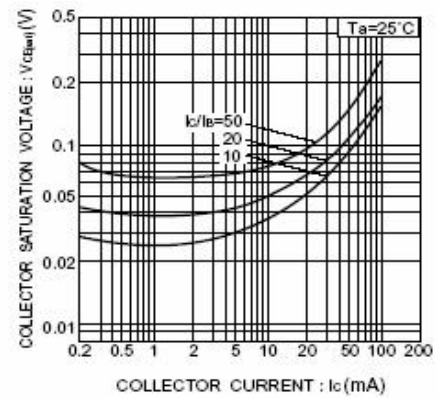


Fig.6 Collector-emitter saturation voltage vs. collector current

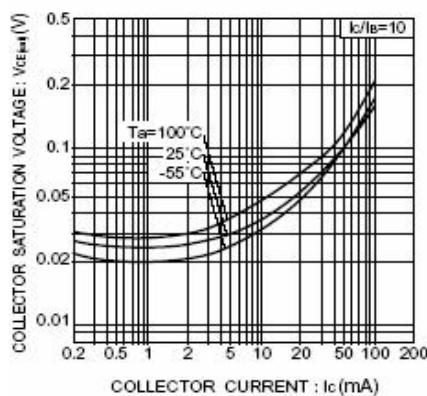


Fig.7 Collector-emitter saturation voltage vs. collector current (I)

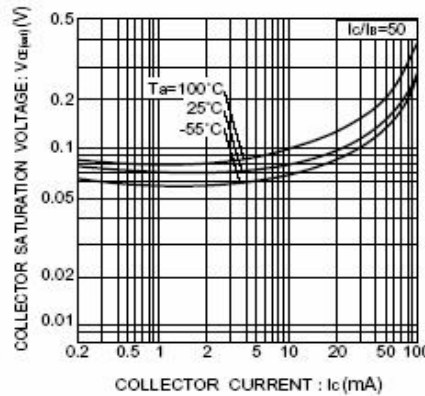


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

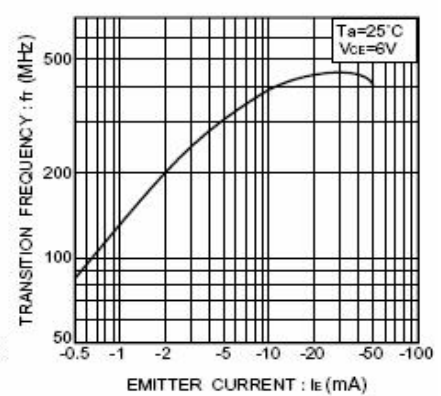


Fig.9 Gain bandwidth product vs. emitter current

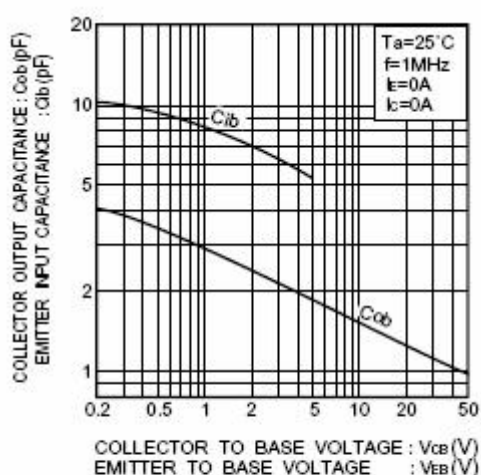


Fig.10 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

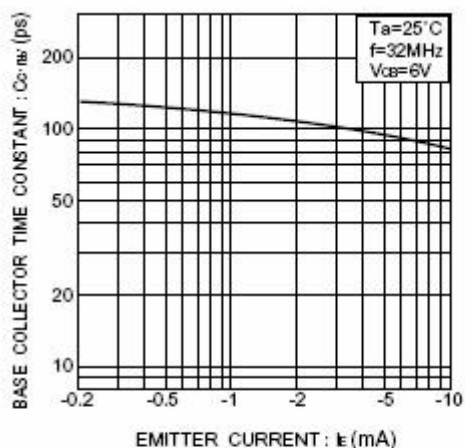
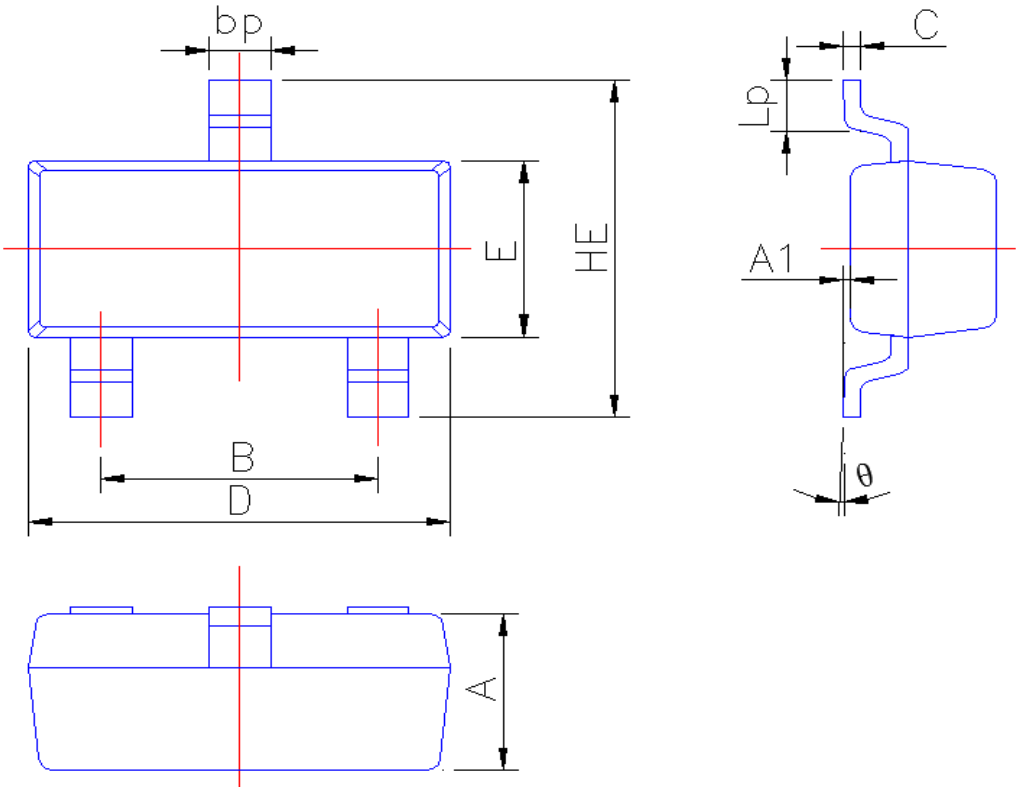


Fig.11 Base-collector time constant vs. emitter current

PACKAGE MECHANICAL DATA



SOT-23

Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°

REELSPECIFICATION

P/N	PKG	QTY
2SC2412R-MS	SOT-23	3000

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